

Abstract of the Disclosure

A high power RF amplifier utilizes dynamic biasing for transistors in an output stage of the amplifier. In one embodiment, as the magnitude of an RF signal to be amplified falls below a predetermined level, the biasing signal is turned off to reduce power consumption. A gate bias voltage is used to switch the transistors off and on. A low pass filter is employed to eliminate noise generated at the output of the amplifier caused by the instantaneous switching, while not impacting the amplifier's response to low-high magnitude transients. In a further embodiment, I and Q data from baseband digital data is sampled and buffered prior to being transformed and provided to a RF power amplifier. A gate bias signal is controlled based on current samples in order to control the power amplifier in a manner appropriate for the current samples when provided from the buffer.

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